

Features

- Glass passivated junctions for greater reliability
- Electrically isolated base plate (3500V RMS)
- Available up to 1200 V_{RRM}, V_{DRM}
- High surge capability
- Large creepage distances
- Simplified mechanical designs, rapid assembly
- B-package case style
- UL E78996 approved

25A

Description

The B25RIA../B25H2S.. series of B-modules consist of power thyristors in single and split configuration in single package. With their isolating base plate, mechanical designs are greatly simplified giving advantages of cost reduction and reduced size.

Applications include power supplies, control circuits, light dimmers and battery chargers.

Major Ratings and Characteristics

Parameters	B25RIA/B25H2S	Units
$I_{T(AV)}$	25	A
@ T_C	70	°C
I_{TSM}	50Hz 390	A
	60Hz 410	A
I^2_t	50Hz 770	A ² s
	60Hz 700	A ² s
$I^2\sqrt{t}$	7700	A ² /s
V _{RRM} range	100 to 1200	V
T _J	-40 to 125	°C



ELECTRICAL SPECIFICATIONS

Voltage Ratings

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Part number	Voltage Code	V_{RRM}, V_{DRM} max peak reverse and off-state leakage current at $V_{RRM}, V_{DRM}, T_J = 125^\circ\text{C}$, gate open circuit mA	V_{RRM}, V_{DRM} maximum repetitive peak reverse and off-state voltage gate open circuit V	V_{RSM} maximum non-repetitive peak reverse voltage V
B25 RIA B25 H2S	10	10	100	150
	20	10	200	300
	40	10	400	500
	60	10	600	700
	80	10	800	900
	100	10	1000	1100
	120	10	1200	1300

On-state Conduction

Parameter	Value	Units	Conditions		
$I_{T(AV)}$ Max. average on-state current	25	A	180° conduction half sine wave @ $T_C = 70^\circ\text{C}$		
$I_{T(RMS)}$ Max. RMS on-state current	40	A			
I_{TSM} Maximum peak one half cycle non repetitive surge current	390	A	10ms	No voltage	Sinusoidal half Wave
	410	A	8.3ms	reapplied	Initial $T_J=125^\circ\text{C}$
	330	A	10ms	100% V_{RRM}	Sinusoidal half Wave
	345	A	8.3ms	reapplied	Initial $T_J=125^\circ\text{C}$
I^2t Maximum I^2t for fusing	770	A^2s	10ms	No voltage	Initial $T_J=125^\circ\text{C}$
	700	A^2s	8.3ms	reapplied	
	545	A^2s	10ms	100% V_{RRM}	Initial $T_J=125^\circ\text{C}$
	490	A^2s	8.3ms	reapplied	
I^2/t Maximum I^2/t for fusing (1)	7700	A^2/s	$t=0$ to 10ms, no voltage reapplied, Initial $T_J=125^\circ\text{C}$		
V_{TM} Maximum peak on-state voltage	1.6	V	$T_J=25^\circ\text{C}$, $I_{TM}=I_{T(AV)} \times \pi$, $t_p=400\mu\text{s}$, 180° conduction		
$V_{T(TO)}$ Max. value of threshold voltage	0.90	V	Low level (3)	$T_J=T_J \text{ max (2)}$	
	1.15	V	High level (4)		
r_t Max. value of on-state slope resistance	12.5	$\text{m}\Omega$	Low level (3)	$T_J=T_J \text{ max (2)}$	
	9.7	$\text{m}\Omega$	High level (4)		
I_H Maximum holding current	100	mA	$T_J=25^\circ\text{C}$ anode supply=6V, resistive load, gate open, Initial $I_T=1\text{A}$		
I_L Maximum latching current	200	mA	$T_J=25^\circ\text{C}$ anode supply=6V, resistive load		
di/dt Maximum rate of rise of off-state voltage					
	$V_{DRM} \leq 600\text{V}$	200	$\text{A}/\mu\text{s}$	$T_J=125^\circ\text{C}$, from $0.67 V_{DRM}$	
	$V_{DRM} = 800\text{V}$	180	$\text{A}/\mu\text{s}$	$I_{TM} = \pi \times I_{T(AV)}$, $I_g = 500\text{mA}$	
	$V_{DRM} = 1000\text{V}$	160	$\text{A}/\mu\text{s}$	$t_r < 0.5\mu\text{s}$, $t_p > 6\mu\text{s}$	
	$V_{DRM} \geq 1100\text{V}$	150	$\text{A}/\mu\text{s}$		

(1) I^2t for time $t_x = I^2/t \times \sqrt{t_x}$

(2) Average power = $V_{T(TO)} \times I_{T(AV)} + r_t \times (I_{T(RMS)})^2$

(3) $16.7\% \times \pi \times I_{T(AV)} < I < \pi \times I_{T(AV)}$

(4) $\pi \times I_{T(AV)} < I < 20 \times \pi \times I_{T(AV)}$

ELECTRICAL SPECIFICATIONS

Triggering

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B5E D

Parameter	B25RIA/B25H2S	Units	Conditions
P_{GM} Maximum peak gate power	8.0	W	
$P_{G(AV)}$ Maximum average gate power	2.0	W	
$+I_{GM}$ Maximum peak gate current	1.5	A	
$-V_{GM}$ Maximum peak negative gate voltage	10	V	
V_{GT} Maximum required DC gate current to trigger	3.0	V	$T_J = -65^\circ\text{C}$
	2.0	V	$T_J = 25^\circ\text{C}$
	1.0	V	$T_J = 125^\circ\text{C}$
I_{GT} Maximum required DC gate current to trigger	90	mA	$T_J = -65^\circ\text{C}$
	60	mA	$T_J = 25^\circ\text{C}$
	35	mA	$T_J = 125^\circ\text{C}$
V_{GD} Maximum gate voltage that will not trigger	0.2	V	@ $T_J = 125^\circ\text{C}$, rated V_{DRM} applied
I_{GD} Maximum gate current that will not trigger	2.0	mA	@ $T_J = 125^\circ\text{C}$, rated V_{DRM} applied

Switching

t_{gd} Typical turn-on time	0.9	μs	$T_J = 25^\circ\text{C}$
t_{rr} Typical reverse recovery time	4	μs	$T_J = 125^\circ\text{C}$ (5)
t_q Typical turn-off time	110	μs	$T_J = 125^\circ\text{C}$ (6)

Blocking

dv/dt Minimum critical rate-of-rise of off-state voltage	100	$V/\mu\text{s}$	$T_J = 125^\circ\text{C}$, Linear to 100% rated V_{DRM}
	300	$V/\mu\text{s}$	$T_J = 125^\circ\text{C}$, Linear to 67% rated V_{DRM}
I_{RRM} Maximum peak reverse and off-state leakage current at V_{RRM} , V_{DRM}	10	mA	$T_J = 125^\circ\text{C}$, gate open circuit
I_{RM} Max. peak reverse leakage current	100	μA	$T_J = 25^\circ\text{C}$
V_{INS} RMS Isolation voltage	3500	V	50Hz, circuit to base, all terminals shorted $T_J = 25^\circ\text{C}$, $t = 1\text{ s}$

Thermal and Mechanical Specifications

T_J Junction temperature range	-40 to 125	$^\circ\text{C}$	
T_{stg} Storage temperature range	-40 to 125	$^\circ\text{C}$	
R_{thJC} Maximum thermal resistance, junction to case	1.05	K/W	Per junction - DC operation
R_{thCS} Max. thermal resistance case to heatsink	0.10/0.20	K/W	Mounting surface smooth flat and greased Per module/Per junction
T Mounting torque $\pm 10\%$	Module to heatsink	1.7	Nm
	Module Terminals	0.45	Nm
wt Approximate weight	40	g	
Case style	"B" Type		See outline table

(5) $I_{TM} = \text{rated } I_{T(AV)}$ for at least 200 μs , $di_{R/dt} = 10\text{ A}/\mu\text{s}$

(6) $I_{TM} = \text{rated } I_{T(AV)}$ for at least 200 μs . Min. V_R during turn-off = 100V, reapplied $dv_{dt} = 20\text{ V}/\mu\text{s}$ linear to 0.80 V_{DRM} - Gate bias 0V, 100 Ω

(7) A mounting compound is recommended and the torque should be rechecked after a period of about 3 hours to allow for the spread of the compound

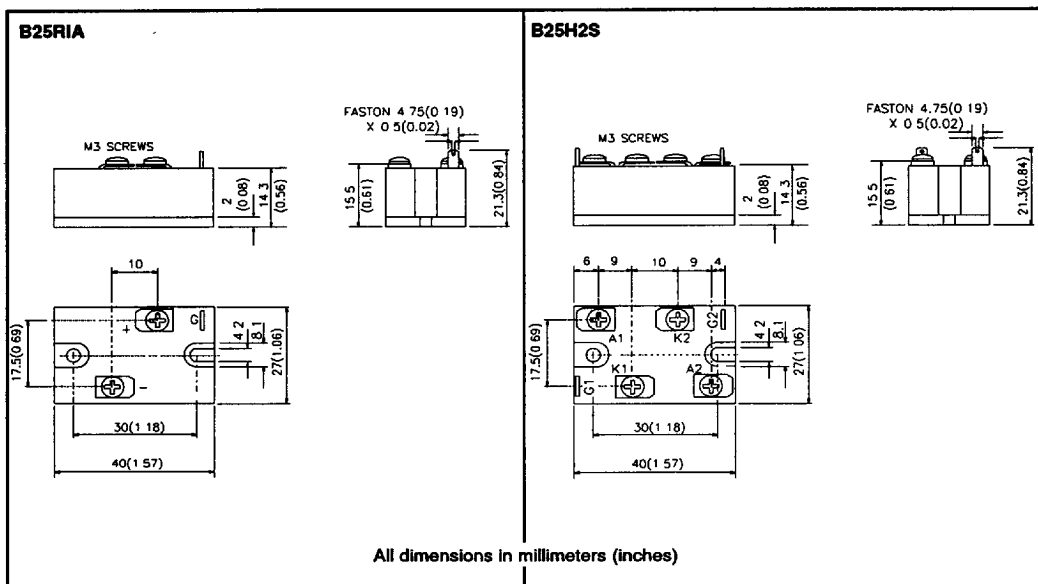
ΔR Conduction (per Junction)

(The following table shows the increment of thermal resistance R_{JUC} when devices operate at different conduction angles than 180°)

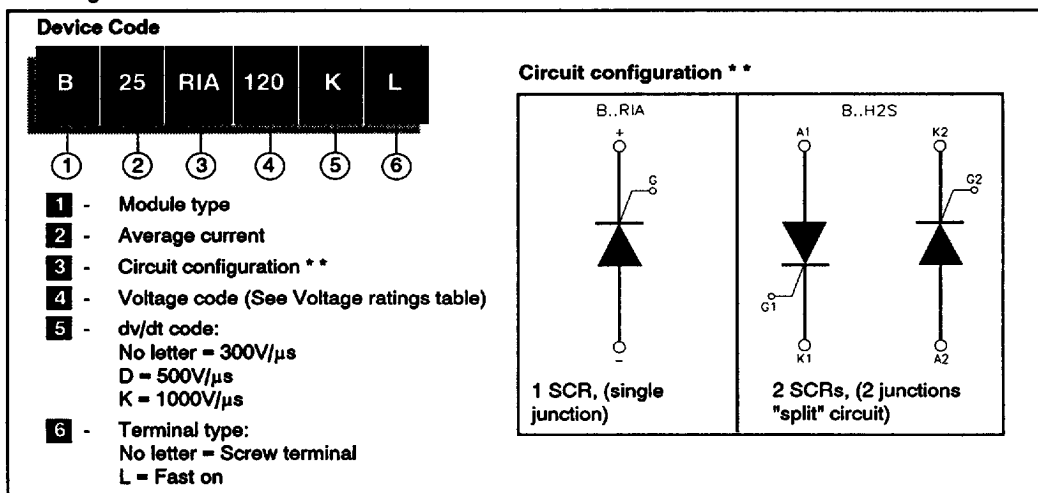
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Conduction angle	Sinusoidal	Rectangular	Units
180°	0.25	0.18	K/W
120°	0.30	0.30	K/W
90°	0.38	0.41	K/W
60°	0.55	0.58	K/W
30°	0.95	0.96	K/W

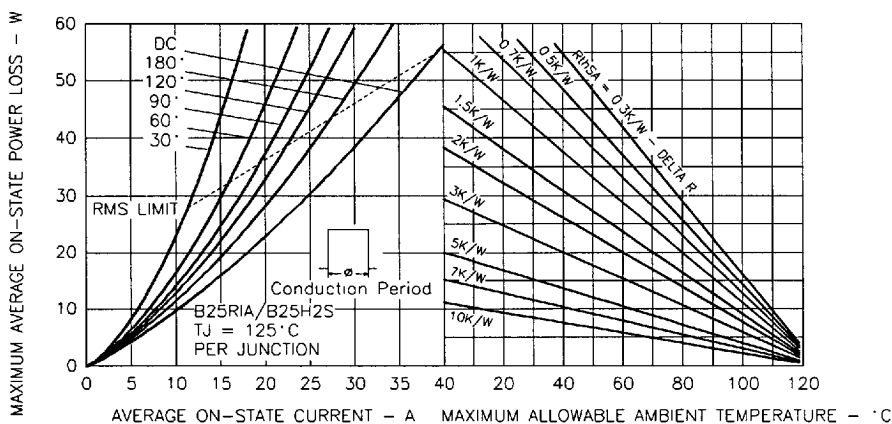
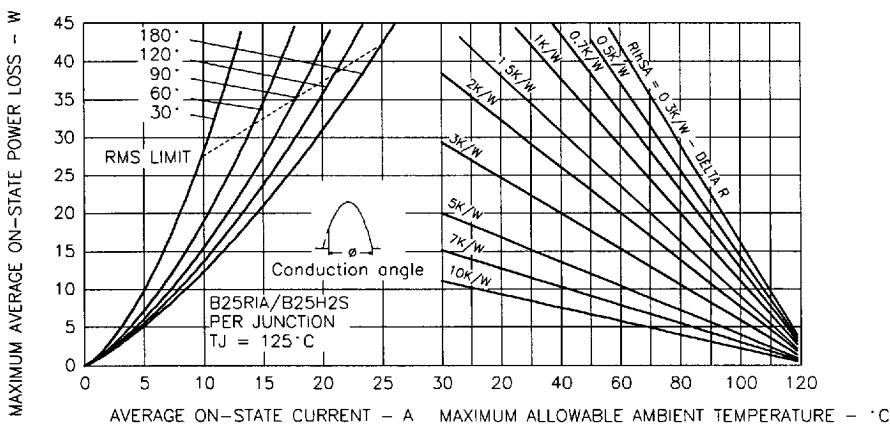
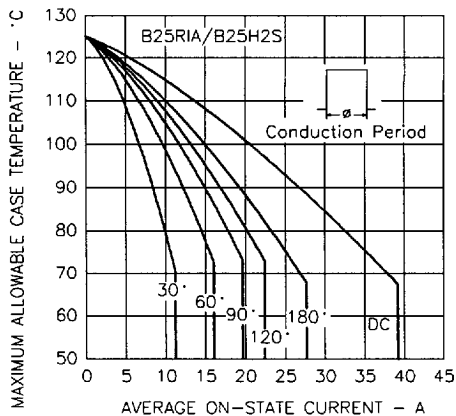
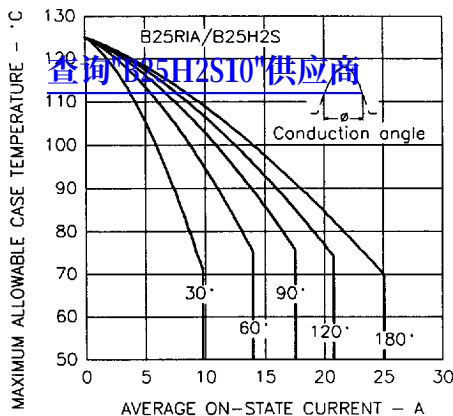
Outlines Table



Ordering Information Table



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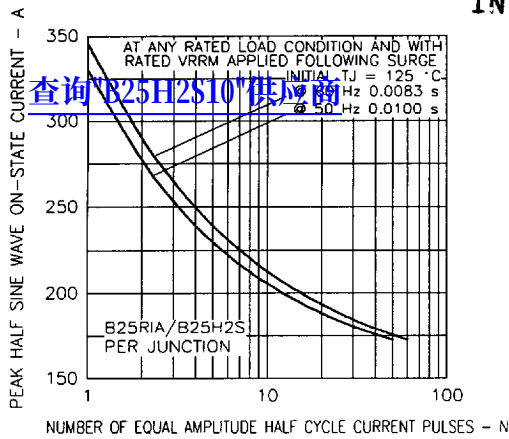


Fig. 5 - Maximum Non-Repetitive Surge Current

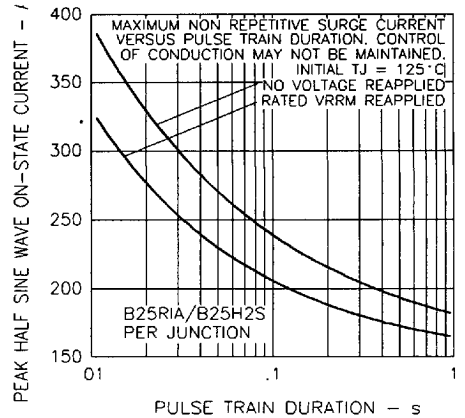


Fig. 6 - Maximum Non-Repetitive Surge Current

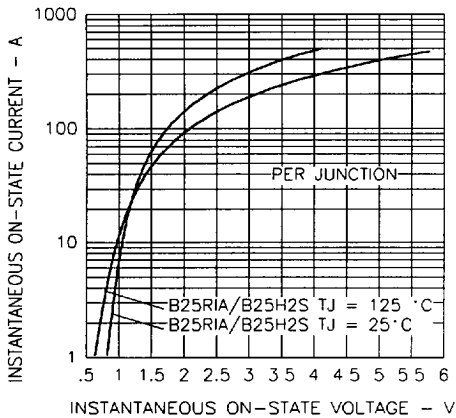


Fig. 7 - On-state Power Loss Characteristics

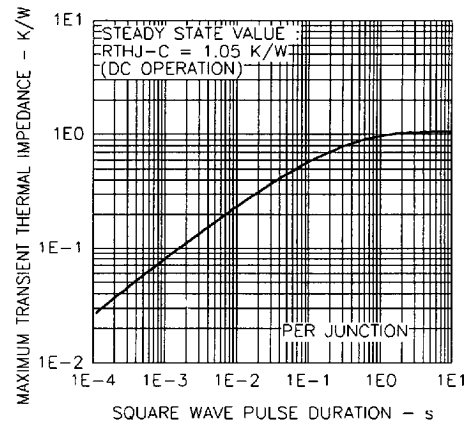
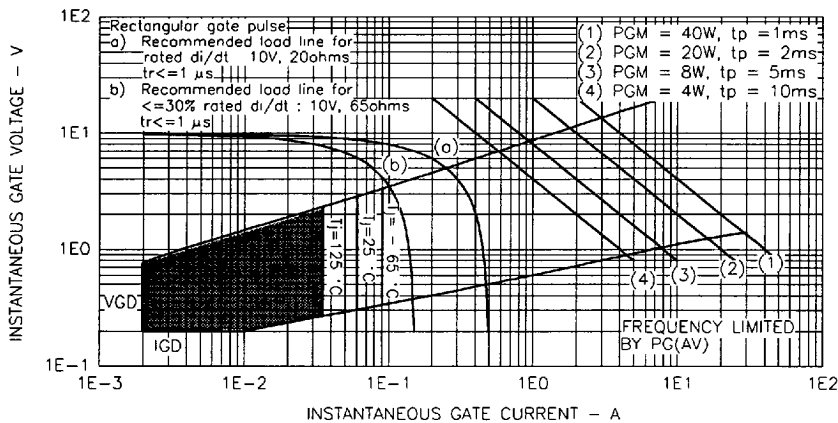
Fig. 8 - Thermal Impedance Z_{thJC} Characteristics

Fig. 9 - Gate Characteristics